

عنوان مقاله:

Compare noise characteristic of DC-HEMT and HEMT

محل انتشار:

دومین کنفرانس بین المللی پژوهش در علوم و تکنولوژی (سال: 1394)

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خلاصه مقاله:

We compare noise characteristics of / DC-HEMT and HEMT. The DC-HEMT exhibits high gain and high current and low noise. The noise characteristics are calculated as a function of gate voltage as well as drain voltage. The noise curve versus gate voltage also shows three regions. And also the noise curve versus drain voltage shows two regions. The first region is related to the triode region of the transistor where the noise decreases with increase of the drain voltage. The second region is related to the saturation region of the transistor where the noise is almost constant.

کلمات کلیدی:

DC-HEMT, noise figure (), AlGa_N , Ga_N

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